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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known	
		Application Number	10/789,042
		Filing Date	February 27, 2004
		First Named Inventor	Kie Y. Ahn
		Group Art Unit	2815
		Examiner Name	Matthew Landau
Sheet 1 of 3		Attorney Docket No: 1303.050US2	

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